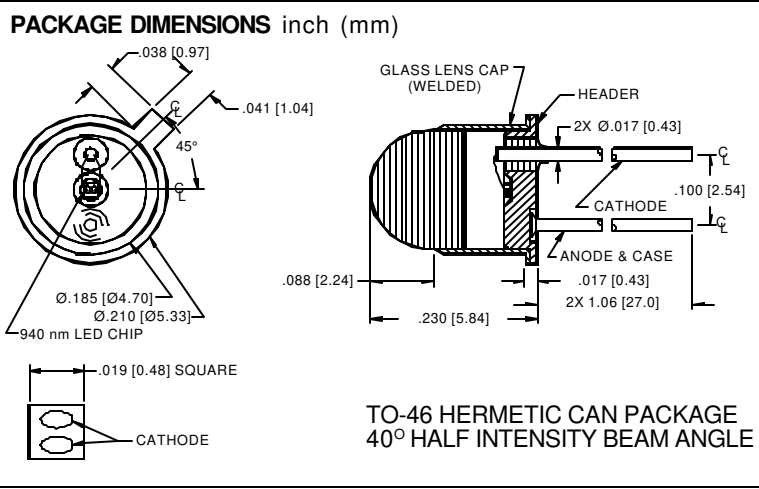
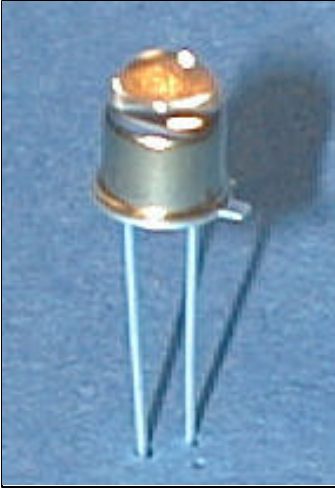


# PHOTONIC DETECTORS INC.

## High-Power & Current GaAs Infrared Emitters Peak Wavelength, 940 nm, Type PDI-E912



### FEATURES

- Dual cathode
- High current
- Medium emission angle

**DESCRIPTION:** The PDI-E912 infrared emitting diode uses dual cathode, high current liquid phase epitaxially grown GaAs. Optimized for high power, and high current at 940 nm. Packaged in a TO-46 can with a glass lens cap.

### APPLICATIONS

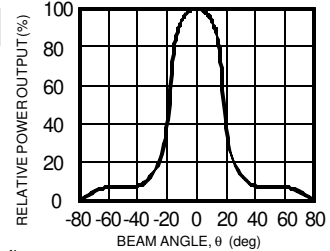
- Photoelectric switches
- Reflective switches
- Smoke detectors

### ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
Pd	Power Dissipation		360	mW
I <sub>FP</sub>	Continuous Forward Current		180	mA
I <sub>FP</sub>	Peak Forward Current (100µs pulse, 10pps)		3.0	A
V <sub>R</sub>	Reverse voltage		3.0	V
To & Ts	Storage & Operating Temperature	-65	+125	°C
TS	Soldering Temperature*		+260	°C

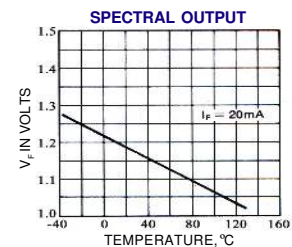
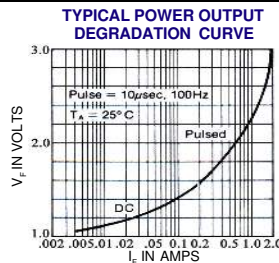
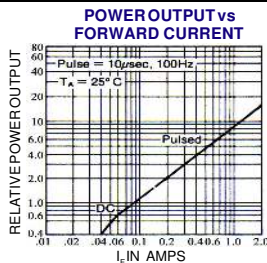
\*1/16 inch from case for 3 secs max

### TYPICAL RADIATION PATTERN



### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P <sub>0</sub>	Output Power	I <sub>F</sub> = 100 mA	1.0	5.0		mW
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 100 mA		1.35	1.75	V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = -3.0 V			10	mA
λ <sub>P</sub>	Peak Wavelength	I <sub>F</sub> = 50 mA	925	940	955	nm
Δλ	Spectral Halfwidth	I <sub>F</sub> = 50 mA		50		nm
R <sub>d</sub>	Dynamic Resistance	I <sub>F</sub> = 100 mA		0.6		Ohm
t <sub>r</sub>	Rise Time	I <sub>F</sub> = 100 mA		1.1		µS
t <sub>f</sub>	Fall Time	I <sub>F</sub> = 100 mA		1.5		mS



Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. Optical power and radiant intensity measured using uncapped dimpled TO-46 into integrating sphere.